Spyridon Pavlidis

List of Publications by Year
in descending order

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29	370	1040056	888059
papers	citations	9	17
		h-index	g-index

29	29	29	577
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Sizeâ€Scalable and Highâ€Density Liquidâ€Metalâ€Based Soft Electronic Passive Components and Circuits Using Soft Lithography. Advanced Functional Materials, 2017, 27, 1604466.	14.9	107
2	Characterization of AlGaN/GaN HEMTs Using Gate Resistance Thermometry. IEEE Transactions on Electron Devices, 2017, 64, 78-83.	3.0	39
3	High gain, large area, and solar blind avalanche photodiodes based on Al-rich AlGaN grown on AlN substrates. Applied Physics Letters, 2020, 116, .	3.3	33
4	Aerosol jet printing for 3-D multilayer passive microwave circuitry. , 2014, , .		25
5	High n-type conductivity and carrier concentration in Si-implanted homoepitaxial AlN. Applied Physics Letters, 2021, 118, .	3.3	25
6	Direct correlation between potentiometric and impedance biosensing of antibody-antigen interactions using an integrated system. Applied Physics Letters, 2017, 111, .	3.3	14
7	Encapsulated Organic Package Technology for Wideband Integration of Heterogeneous MMICs. IEEE Transactions on Microwave Theory and Techniques, 2017, 65, 438-448.	4.6	11
8	A 5.4W X-band gallium nitride (GaN) power amplifier in an encapsulated organic package. , 2015, , .		10
9	Study on avalanche breakdown and Pooleâ€“Frenkel emission in Al-rich AlGaN grown on single crystal AlN. Applied Physics Letters, 2021, 119, .	3.3	10
10	Chemical treatment effects on Schottky contacts to metalorganic chemical vapor deposited n-type N-polar GaN. Journal of Applied Physics, 2020, 128, 064501.	2.5	9
11	Largeâ€Area, Solarâ€Blind, Subâ€250 nm Detection AlGaN Avalanche Photodiodes Grown on AlN Substrates. Physica Status Solidi - Rapid Research Letters, 2022, 16, .	2.4	9
12	Record >10â€‰MV/cm mesa breakdown fields in Al0.85Ga0.15N/Al0.6Ga0.4N high electron mobility transistors on native AlN substrates. Applied Physics Letters, 2022, 120, .	3.3	9
13	Integrated microfluidic cooling for GaN devices on multilayer organic LCP substrate. , 2013, , .		8
14	A feasibility study of flip-chip packaged gallium nitride HEMTs on organic substrates for wideband RF amplifier applications. , 2014, , .		8
15	A low-cost, encapsulated flip-chip package on organic substrate for wideband gallium nitride (GaN) hybrid amplifiers. , 2014, , .		8
16	GaN lateral polar junction arrays with 3D control of doping by supersaturation modulated growth: A path toward III-nitride superjunctions. Journal of Applied Physics, 2022, 131, 015703.	2.5	8
17	Role of polarity in SiN on Al/GaN and the pathway to stable contacts. Semiconductor Science and Technology, 2020, 35, 055007.	2.0	7
18	p-n-p-Based RF Switches for the Mitigation of Single-Event Transients in a Complementary SiGe BiCMOS Platform. IEEE Transactions on Nuclear Science, 2018, 65, 391-398.	2.0	6

#	Article	IF	Citations
19	(Invited) A Path Toward Vertical GaN Superjunction Devices. ECS Transactions, 2020, 98, 69-79.	0.5	6
20	On the Ge shallow-to-deep level transition in Al-rich AlGaN. Journal of Applied Physics, 2021, 130, .	2.5	5
21	An Electrostatic Discharge Protection Circuit Technique for the Mitigation of Single-Event Transients in SiGe BiCMOS Technology. IEEE Transactions on Nuclear Science, 2018, 65, 426-431.	2.0	4
22	3-D printed substrates for MMIC packaging. , 2017, , .		3
23	On the characteristics of N-polar GaN Schottky barrier contacts with LPCVD SiN interlayers. Applied Physics Letters, 2021, 118, .	3.3	3
24	A hybrid GaN/organic X-band transmitter module. , 2013, , .		2
25	Fabrication and characterization of CPW transmission lines with CoFe<inf>2</inf>O<inf>4</inf> nanomagnetic thin films. , 2017, , .		1
26	A hybrid GaN/organic X-band transmitter module. , 2013, , .		0
27	Room temperature CO<inf>2</inf> detection using interdigitated capacitors with heteropolysiloxane sensing films. , 2016, , .		0
28	Schottky contacts to N-polar GaN with SiN interlayer for elevated temperature operation. Applied Physics Letters, 2022, 120, .	3.3	0
29	(Invited, Digital Presentation) Exploring Interfaces and Polarity to Realize Vertical III-Nitride Superjunction Devices. ECS Meeting Abstracts, 2022, MA2022-01, 1313-1313.	0.0	0